

Date	User	Material	Recipe	Substrate T	Measured Thickness	Target Th.	Target+10%	Target-10%	AVG			Dep.time	Dep.time	JAW EC-400 (Woolam Spectroscopic		AVG index	AVG+2%	AVG-2%	Dep.rate	Stress	HF etch rate		LPD (light point defects)		AVG			Additional Notes	
									Thick.	AVG+10%	AVG-10%			Index @632.8nm	Index@1550nm						(nm/min)	(+456MPa)	(nm/min)	before dep.	after dep.	dep.rate	AVG+10%		AVG-10%
1/1/2012	User	SIN	SIN_10	250 C	(Å)	1000A	1100A	900A	1022A			min/sec	sec																
01/06/14	Biljana	SIN	SIN_10	250	1055.81	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.949	1.903	1.939	1.978	1.900	11.15	571.87		78	547	11.27	12.39	10.14	4"	Si wafer	
01/23/14	Biljana	SIN	SIN_10	250	1133.40	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.935	1.890	1.939	1.978	1.900	11.97	446.88	90.66	137	377	11.27	12.39	10.14	4"	Si wafer	
02/03/14	Biljana	SIN	SIN_10	250	1046.60	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.937	1.893	1.939	1.978	1.900	11.05	486.75	81.21	322	604	11.27	12.39	10.14	4"	Si wafer	
02/19/14	Biljana	SIN	SIN_10	250	1030.66	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.935	1.890	1.939	1.978	1.900	10.89	353.92	77.32	75	323	11.27	12.39	10.14	4"	Si wafer	

Target Thicl 1000.00
 Target+10% 1100.00
 Target-10% 900.00
 Avg Thicl 1066.62
 Avg +10% 1173.28
 Avg - 10% 959.96

Avg index@6 1.939
 Avg+2% 1.978
 Avg-2% 1.900

Avg. Rate 11.27
 Avg +10% 12.39
 Avg - 10% 10.14

